

Number	Hits	Search Text	DB	Time stamp
1	1	"112'0965"	JPO	2002/06/13 14:56
2	0	"ip11250965"	JPO	2002/06/13 15:01
3	0	6433447.pn. and (sealing plate).clm.	JPO	2002/06/13 15:01
4	0	6433447.pn. and (adhesive sealing plate).clm.	JPO	2002/06/13 15:01
5	0	6433447.pn. and (sealing plate).clm.	USPAT	2002/06/13 15:01
6	1	6433447.pn.	USPAT	2002/06/13 15:53
7	0	patel-washok.xp. and preferred adj embossments	USPAT	2002/06/13 15:53
8	0	patel-washok.xp. and preferred adj embossments	USPAT	2002/06/13 15:53
-	229	(445/25).CCLS.	USPAT	2002/08/13 14:39
-	343	(313/512).CCLS.	USPAT	2002/08/13 14:39
-	0	09671654.ap.	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:39
-	1	9671654.ap.	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:39
-	229	(445/25).CCLS.	USPAT	2002/08/13 14:43
-	722	((313/512) or (445/25)).CCLS.	USPAT; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:43
-	17	((313/512) or (445/25)).CCLS.) and active adj matrix	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:55
-	13	((313/512) or (445/25)).CCLS.) and active adj matrix) and crystal	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:56
-	1	((313/512) or (445/25)).CCLS.) and active adj matrix) and single adj crystal	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 14:58
-	3	5872183.UEPN.	USPAT	2002/08/13 14:57
-	1	((313/512) or (445/25)).CCLS.) and active adj matrix) and (field adj effect adj transistor FET)	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 15:01
-	0	(257/5).ccls.	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 15:01
-	134751	(257/5).ccls.	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 15:02
-	66945	(313/5).ccls.	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 15:02
-	8	((27/5).ccls.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET)	USPAT; US-PGFPUB; EPC; JPO; DEFWENT; IRM_TDB	2002/08/13 15:04

Search History 6/14/05 3:57:25 PM Page 2
C:\APPS\east\workspace\09671654.wsp

1	("6351010").PN.	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 07:37
2	("6153893" "6246070").PN.	USPAT	2002/08/29 07:47
6	((("6153893" "6246070").PN.) and organic with EL electroluminescence electroluminescent.	USPAT	2002/08/29 07:46
0	((("6153893" "6246070").PN.) and organic same EL electroluminescence electroluminescent	USPAT	2002/08/29 07:46
3	semiconductor-energy-laboratory.as.	USPAT	2002/08/29 07:43
4	semiconductor-energy-laboratory.as.	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 07:51
7	single.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 07:55
2	single.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:00
(single.as. and single adj crystal and active adj matrix and gate with (FET field adj effect adj transistor) and (organic with (EL electroluminescent electroluminescence) and inert	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:00
2	((((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/311) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with EL) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:38
2	((((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/311) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET) and single adj crystal	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:43
8	((((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/311) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:44
8	((((257/57) or (257/59) or (257/66) or (257/68) or (257/71) or (257/347) or (257/311) or (313/512) or (445/25)).CCLS.) and active adj matrix and (organic with (EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and gate	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 08:44

2	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/247) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni)	USPAT; US-PGPUB; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:21
3	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:24
3	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 11:12
3	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:26
3	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:27
1	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni) and (barium adj oxide silica adj gel drying)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:28
1	(1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/380) or (313/512) or (445/25).CCLS.) and active adj matrix and (organic with EL electroluminescence electroluminescent) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium he argon ar krypton kr xenon xe nitr gen ni) and (barium adj oxide silica adj gel drying)	USPAT; EPC; JPO; DEFWENT; IBM_TDB	2002/08/29 10:28

-	1	(157/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and helium ne argon or krypton kr xenon xe nitrogen ni)) and (helium ne argon or krypton kr xenon xe nitrogen n inert adj gas inert adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 10:29
-	1	(157/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL electroluminescence electroluminescent)) and gate with (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and helium ne argon or krypton kr xenon xe nitrogen ni)) and (helium ne argon or krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:14
-	4	(157/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:20
-	1	(157/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and active adj matrix and organic with (EL electroluminescence electroluminescent)) and field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal and (helium ne argon or krypton kr xenon xe nitrogen n inert adj gas rare adj gas) and (barium adj oxide silica adj gel drying)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:15
-	4	(157/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or (313/512) or (445/25)).CCLS.) and matrix and organic with (EL electroluminescence electroluminescent)) and (field adj effect adj transistor FET bottom adj gate top adj gate) and single adj crystal	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/06/12 14:12
-	1075	313 514	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 11:58
-	0	313 514,510	USPAT; US-PGPUB	2002/08/29 11:58
-	1650	313 514 313 500	USPAT; US-PGPUB	2002/08/29 12:20
-	1075	313 514	USPAT; US-PGPUB	2002/08/29 12:21
-	1064	(313 504) or (313/500)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/29 12:36

-	116 (((313/504) or (313/500)).CCLS.) AND Active adj matrix	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:21
-	114 (((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:23
-	9 (((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet) and single adj crystal	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 13:32
-	7 (((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet) and single adj crystal) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:28
-	7 (((313/504) or (313/500)).CCLS.) AND Active adj matrix and (field effect transistor fet) and single adj crystal) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:36
-	0 20020074448.05FEN.	USPAT	2001/08/29 12:35
-	810 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:37
-	530 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen n) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:38
-	407 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:39
-	2 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (envelope vacant vacancy) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:40
-	181 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) and (organic adj EL organic adj layer) and (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:41
-	57 (((313/504) or (313/500)).CCLS.) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel) and (organic adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:44
-	615 (((313/504) or (313/500)).CCLS.) and (inert adj EL organic adj layer)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:44
-	57 (((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:45
-	57 (((313/504) or (313/500)).CCLS.) and (organic adj EL organic adj layer) and (inert adj gas rare adj gas helium he krypton kr argon ar xenon xe nitrogen) same (barium adj oxide silica gel)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2001/08/29 12:47

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USPAT;                2002/08/29 13:33
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB
USPAT;                2002/08/29 13:32
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB
USPAT;                2002/08/29 13:53
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

USPAT;                2002/08/29 13:54
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

USPAT;                2002/08/29 13:57
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB
USPAT;                2002/08/29 14:00
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

USPAT;                2002/08/29 14:01
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

USPAT;                2002/08/29 14:03
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

USPAT;                2002/08/29 14:03
US-PGPUB;
EPC; JPC;
DEFWENT;
IRM_TDB

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-	1	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB	2002/08/29 14:23
-	2	("61"5186").PN;	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/08/29 14:04
-	24	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/08/29 14:06
-	10	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/08/29 14:27
-	1	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and possible	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/08/29 14:35
-	1	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic and (EL electroluminescent electroluminescence) and (barium adj oxide silica adj gel)	USPAT; US-PGPUB	2002/08/29 14:23
-	1	pp10/8476	JPT	2002/03/29 14:24
-	15	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and active adj matrix and (FET field adj effect adj transistor) and organic with (EL electroluminescent electroluminescence)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/03/29 15:53
-	537	(1257/57; or (257/59) or (257/66) or (257/68) or (257/72) or (257/347) or (257/350) or (313/512) or 445/25) or (313/500) or (313/504) or (313/445)).CCLS.; and organic with (EL electroluminescent electroluminescence) and (helium he nitrogen krypton kr argon ar xenon xe) and (barium oxide silica adj gel)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/08/29 14:36

-	11	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or (445/25) or (313/504) or 313/504) or (313/495)).OCLS.) and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel and goggle	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 14:41
-	0	jp1003065	JPO	2002/08/29 14:42
-	0	semiconductor adj laboratory and yamazaki and "1998"	JPO	2002/08/29 14:43
-	5179	yamazaki and "1998"	JPO	2002/08/29 14:43
-	0	yamazaki and "1998" and semiconductor adj energy adj laboratory	JPO	2002/08/29 14:43
-	0	10-333665 and yamazaki	JPO	2002/08/29 14:48
-	0	"10333665" and yamazaki	JPO	2002/08/29 14:48
-	0	"10333665" and yamazaki	JPO	2002/08/29 14:48
-	0	"jp10333665" and yamazaki	JPO	2002/08/29 14:48
-	0	"jp10333665" and yamazaki	JPO	2002/08/29 14:48
-	0	"jp10333665"	JPO	2002/08/29 14:48
-	0	"jp10333665"	JPO	2002/08/29 14:48
-	0	"jp10333665"	JPO	2002/08/29 14:48
-	366	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or (445/25) or (313/504) or 313/504) or (313/495)).OCLS.) and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 14:50
-	83	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or (445/25) or (313/504) or 313/504) or (313/495)).OCLS.) and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) and barium oxide silica adj gel	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 14:51
-	36	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or (445/25) or (313/504) or 313/504) or (313/495)).OCLS.) and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) same barium adj oxide silica adj gel	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 14:52
-	3	((257/57) or (257/59) or (257/66) or (257/66) or (257/72) or (257/347) or (257/350) or 313/512) or (445/25) or (313/504) or 313/504) or (313/495)).OCLS.) and organic with (EL electroluminescent electroluminescence) and helium he nitrogen krypton kr argon ar xenon xe) same barium adj oxide silica adj gel	USPAT; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 14:55
-	7	("5739945" "5747930" "5834834" "5837713" "6046543" "6246173" "6307324").PN.	USPAT	2002/08/29 14:54
-	2	("6175186").PN.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:13

-	0	(313/3 and ceramic with transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
-	0	(313/3 and ceramic same transparent).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
-	0	(313/3 and ceramic same clear).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
-	66966	(313/3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:27
-	0	((313/3).CCLS.) and nitride adj ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 15:28
-	359	((313/3).CCLS.) and ceramic with (clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 16:50
-	0	((257/57) or (257/59) or (257/66) or (257/66) or (257/70) or (257/340) or (257/350) or (313/510) or (445/25) or (313/300) or (313/304) or (313/400).CCLS.) and active adj matrix with joggle	USPAT	2002/08/29 15:54
-	24	((257/57) or (257/59) or (257/66) or (257/66) or (257/70) or (257/340) or (257/350) or (313/510) or (445/25) or (313/300) or (313/304) or (313/400).CCLS.) and display with joggle	USPAT	2002/08/29 15:59
-	0	EP01481563	JPO	2002/08/29 15:58
-	0	EP01481563	JPO	2002/08/29 15:58
-	25	((257/57) or (257/59) or (257/66) or (257/66) or (257/70) or (257/340) or (257/350) or (313/510) or (445/25) or (313/300) or (313/304) or (313/400).CCLS.) and display same joggle	USPAT	2002/08/29 15:59
-	25	((257/57) or (257/59) or (257/66) or (257/66) or (257/70) or (257/340) or (257/350) or (313/510) or (445/25) or (313/300) or (313/304) or (313/400).CCLS.) and display and joggle	USPAT	2002/08/29 16:46
-	9	nitride adj ceramic with (transparent clear)	USPAT	2002/08/29 16:47
-	0	nitride adj ceramic with oxide with glass with (transparent clear)	USPAT	2002/08/29 16:47
-	23	((313/3).CCLS.) and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 16:52
-	0	((313/3).CCLS.) and nitride adj ceramic same (transparent clear)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/08/29 16:51

-	20	((313/51).CCLS.) and nitride with ceramic same (display clear transparent transparency)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:07
-	0	jp102854476	JP	2002/08/29 17:07
-	0	jp102854476	JP	2002/08/29 17:07
-	0	jp0102854476	JP	2002/08/29 17:12
-	3	("6351010").PN.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:13
-	0	("1459 and yamanaka and insulated adj gate").PN.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:13
-	8	((1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and yamanaka and insulated adj gate	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:16
-	0	((1257/57) or (257/59) or (257/66) or (257/66) or (257/71) or (257/347) or (257/350) or (313/512) or (445/25) or (313/500) or (313/504) or (313/495)).CCLS.) and insulated adj gate	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:17
-	3	and organic adj layer sony,as. and insulated adj gate adj field and organic	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2002/08/29 17:18
-	329	yamazaki-shunpei.in. or arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
-	22	yamazaki-shunpei.in. and arai-yasuyuki.in.	US-PGPUB	2003/06/11 18:07
-	21	yamazaki-shunpei.in. and arai-yasuyuki.in. and organic	US-PGPUB	2003/06/12 11:17
-	9	"passivation film 847"	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 10:56
-	0	"passivation film 847 is formed on the anode layer 846"	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 11:01
-	0	"passivation film 847 is formed on the anode layer 846."	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 10:57
-	1420	semiconductor adj device adj method adj fabricating	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 11:00
-	745	semiconductor adj device adj method adj fabricating.ti.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 11:01
-	0	"passivation film 847 is formed"	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TIB	2003/06/12 11:02
-	0	yamazaki-shunpei.in. and arai-yasuyuki.in. and suakami-satoshi.in.	US-PGPUB	2003/06/12 11:18

-	1	yamazaki-shunpei.in. and arai-yasuyuki.in. and murakami-satoshi.in.	US-PGPUB	2003/06/12 11:19
-	2171	(313/312) or 313/304) or (312/500) or (445/24)).CCLS.	USPAT	2003/06/12 15:58
-	237	(OLED organic adj3 el adj3 (device display)).bi. and (FET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:07
-	315	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).bi. and (FET field adj effect adj transistor).bi.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
-	166	(OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).bi. and (FET field adj effect adj transistor).bi.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:08
-	98	((OLED organic adj3 el adj3 (device display) organic adj2 (electroluminescent electroluminescence).bi. and (FET field adj effect adj transistor).bi.) and (matrix matrices)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:09
-	52	((FET organic adj3 el adj3 device display) organic adj2 (electroluminescent electroluminescence).bi. and (FET field adj effect adj transistor).bi.) and (matrix matrices); and gas nitrogen krypton xenon argon neon helium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:16
-	36	((FET organic adj3 el adj3 device display) organic adj2 (electroluminescent electroluminescence).bi. and (FET field adj effect adj transistor).bi.) and (matrix matrices); and gas nitrogen krypton xenon argon neon helium) and (dry drying desiccant getter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 16:27
-	36	US-6111553-S or US-6110113-S or US-6214510-S or US-6134119-S or US-6111117-S or US-6140109-S or US-6114017-S or US-6113558-S or US-6035710-S or US-6035881-S or US-6073540-S or US-6443182-S or US-6134415-S or US-6133444-S or US-6141151-S or US-6138135-S or US-6410701-S or US-6413004-S or US-6311518-S or US-6344664-S or US-6311010-S or US-6346713-S or US-6421126-S or US-6391116-S or US-6511515-S or US-6115994-S).did. or US-6142115-S or US-6511831-S or US-6431190-S or US-6483564-S or US-6443715-S or US-6439584-S or US-6444884-S).did. or (EP-1085595-S).did. or (JP-2001167877-S).did. or (EP-1085595-S).did.	USPAT; EPO; JPO; DERWENT	2003/06/12 16:18

USPAT; 2003/06/12 16:19
EPO; JPO;
DEEWENT

USPAT; 2003/06/12 16:51
EPO; JPO;
DEFWENT

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USPAT;          2003/06/12 19:01
EPO; JPO;
DEFWENT;
IBM4 TDB
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USPAT; 2003/06/12 16:44
EPO; JPO;
DEFWENT;
IBM.TDB

USPAT; 2003/06/12 17:56
EPO; JPO;
IBM TDB

87 //US-6383664-\$ or US-3665238-\$ or
 US-6210215-\$ or US-4204121-\$ or
 US-5766053-\$ or US-5863464-\$ or
 US-5997378-\$ or US-6037110-\$ or
 US-6067832-\$ or US-6424042-\$ or
 US-6150406-\$ or US-6380178-\$ or
 US-6351110-\$ or US-6150111-\$ or
 US-6351178-\$ or US-6356012-\$ or
 US-6441581-\$ or US-6175116-\$ or
 US-6180445-\$ or US-5565040-\$ or
 US-6061366-\$ or US-5771510-\$ or
 US-6011177-\$ or US-5664216-\$ or
 US-6081761-\$ or US-6000411-\$).did. or
 (US-6302558-\$ or US-6107118-\$ or
 US-6404501-\$ or US-6264441-\$ or
 US-6000041-\$ or US-6037081-\$ or
 US-6004374-\$ or US-6151711-\$ or
 US-6004472-\$ or US-6355044-\$ or
 US-6501666-\$ or US-6127722-\$ or
 US-6401149-\$ or US-6095040-\$ or
 US-6317036-\$ or US-6436141-\$ or
 US-6047790-\$ or US-6757116-\$ or
 US-6001011-\$ or US-6078621-\$ or
 US-6104111-\$ or US-6186111-\$ or
 US-6311113-\$ or US-6411111-\$ or
 US-6111071-\$ or US-6111111-\$ or
 US-6404422-\$).did. or (US-6514700-\$ or
 US-6510921-\$ or US-6522019-\$ or
 US-6514439-\$ or US-6460410-\$ or
 US-6460460-\$ or US-6448710-\$ or
 US-6460121-\$ or US-6369007-\$ or
 US-6149187-\$ or US-6411019-\$ or
 US-6360268-\$ or US-6409719-\$).did. or
 (US-10010064131-\$ or US-1001017643-\$ or
 US-10010074931-\$ or US-10020014746-\$ or
 US-10010046573-\$ or US-10010050532-\$ or
 US-10020018911-\$ or US-10020045397-\$ or
 US-10010050785-\$).did. or
 (EP-1730595-\$.did.) and organic

USPAT; 2003/06/12 19:00
 US-PGPUB;
 EPO; JPO;
 DERWENT;
 IBM_TDB

2003/06/12 19:01

16 ((US-6383664-\$ or US-3665236-\$ or
 US-6210215-\$ or US-4204721-\$ or
 US-5760053-\$ or US-5883464-\$ or
 US-5997578-\$ or US-6037710-\$ or
 US-6061931-\$ or US-6424042-\$ or
 US-6359606-\$ or US-6380582-\$ or
 US-6351010-\$ or US-6156187-\$ or
 US-6251178-\$ or US-6350017-\$ or
 US-6441553-\$ or US-6175176-\$ or
 US-6183465-\$ or US-5563645-\$ or
 US-5661364-\$ or US-5771562-\$ or
 US-5811177-\$ or US-5864106-\$ or
 US-5883701-\$ or US-5904011-\$).did. or
 (US-6372558-\$ or US-6102548-\$ or
 US-6426591-\$ or US-6284347-\$ or
 US-6328941-\$ or US-6537057-\$ or
 US-6378374-\$ or US-6551724-\$ or
 US-6834737-\$ or US-6553963-\$ or
 US-6561656-\$ or US-6137742-\$ or
 US-4958149-\$ or US-6005141-\$ or
 US-5317226-\$ or US-6431111-\$ or
 US-5896821-\$ or US-6757126-\$ or
 US-5703171-\$ or US-6078624-\$ or
 US-6171114-\$ or US-6187304-\$ or
 US-6196111-\$ or US-6417311-\$ or
 US-6401111-\$ or US-6111357-\$ or
 US-6493476-\$).did. or US-6517700-\$ or
 US-6820811-\$ or US-6531113-\$ or
 US-6826634-\$ or US-6463473-\$ or
 US-6462443-\$ or US-6418719-\$ or
 US-6466111-\$ or US-6369503-\$ or
 US-644147-\$ or US-6411133-\$ or
 US-6862461-\$ or US-6487719-\$).did. or
 (US-20000663181-\$ or US-2000017643-\$ or
 US-20020074935-\$ or US-2002004746-\$ or
 US-20010046578-\$ or US-2010090532-\$ or
 US-20000018911-\$ or US-20020045397-\$ or
 US-20020050785-\$).did. or
 (EP-1039595-\$).did. and (organic) and (tft
 field adj effect adj 3 transistor fet)) and
 (gas nitrogen krypton xenon argon neon
 helium)

USBAT; 2003/06/12 19:02
 EPO; JPO;
 DERWENT;
 IBM_TDB

USPAT; 2003/06/13 13:14
US-IPUB;
EPO; JPO;
DERWENT;
IBM TDB

USPAT; 2003/06/13 12:12
EPL; JPO;
IBM TCR

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IBM TDB
USFAT;      2003/06/13 12:12
EPB; CP.;
IBM TDB
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IBM TDB
USEAT; 2003/06/13 12:29
EPD; JPD;
IBM TDB

IBM TDB
USPÄT; 2003/06/13 12:42
EPA; JPA;
IBM TDB

US:AT; 2003/06/13 12:35
EEO; JED;
IBM TDR

USPÄT; 2003/06/13 12:48
EFC; JED;
IEN TDE

USFAT: 2003/06/13 12:57

USIAT; 2003/06/13 12:42
EFL; JLD;
IPN TRF

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IP: TDE
US: AT;      2003/06/13 12:42
EP: JID;
IP: TDE
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IBM TDE
USFAT; 2003/06/13 13:14
EPO; JFO;
IBM TDE

[illegible]

-	2 (6433487.pn. 6555969.pn.) and (tft) and single adj3 (crystal crystalline)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/13 13:20
-	2 (6433487.pn. 6555969.pn.) and (tft) and single adj3 (crystal crystalline) and semiconductor adj2 film with (si silicon)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/13 13:22
-	2 (6433487.pn. 6555969.pn.) and active adj matrix	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2003/06/13 14:58